Application No.: Not Yet Assigned Docket No.: 20136-00342-US1

AMENDMENTS TO THE CLAIMS

1. (Cancelled)

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- 2. (Cancelled)
- 3. (Cancelled)
- 4. (Original) A method of manufacturing an integrated circuit transformer comprising:

forming a first metallization layer on a substrate comprising a first plurality of turns of a first winding:

forming an insulating layer over said first metallization layer;

forming a second metallization layer on said insulating layer comprising a second plurality of turns of a second winding, and a third plurality of turns of a third windings; and

connecting one end of said second winding to one end of said first winding whereby a primary winding is provided for said transformer and said third winding comprises a secondary for said transformer.

- 5. (Original) The method according to claim 4 further comprising forming a via in said insulating layer and connecting said one end of said second winding to said one end of said first winding through said via.
- 6. (Original) The method according to claim 4 wherein said second plurality of turns of said second winding are separated by said third plurality of turns of said third winding.

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7. (Original) The method according to claim 4 further comprising:

forming a fourth set of a plurality of turns of a fourth winding on said first metallization layer to form a second secondary winding for said transformer.

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- 8. (Original) The method according to claim 7 wherein each turn of said fourth winding is separated from each other by said first plurality of turns of said transformer winding.
 - 9. (Original) The method according to claim 4 comprising:

forming an insulating layer over a region of a substrate having semiconductor devices; and

forming said first metallization layer on said insulating layer.

10. (Original) The method according to claim 9 wherein said insulating layer comprises SiO2.